



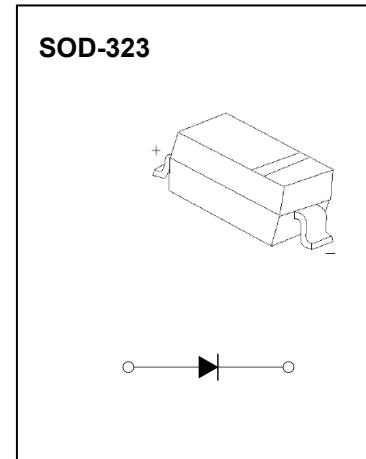
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOD-323 Plastic-Encapsulate Diodes

RB501V -40 Schottky Barrier Diode

FEATURES

- Low current rectifier schottky diode
- Low voltage, low inductance
- For power supply



MAKING: 4

Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	Limit		Unit
Peak reverse voltage	V _{RM}	45		V
DC reverse voltage	V _R	40		V
Mean rectifying current	I _O	0.1		A
Peak forward surge current	I _{FSM}	1		A
Power dissipation	P _D	200		mW
Thermal Resistance Junction to Ambient	R _{θJA}	500		°C/W
Junction temperature	T _j	125		°C
Storage temperature	T _{stg}	-55~+150		°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V _F			0.55 0.34	V	I _F =100mA I _F =10mA
Reverse current	I _R			30	μA	V _R =10V
Capacitance between terminals	C _T		6		pF	V _R =10V, f=1MHZ